

Silicon PNP Power Transistors

2SA969

**DESCRIPTION**

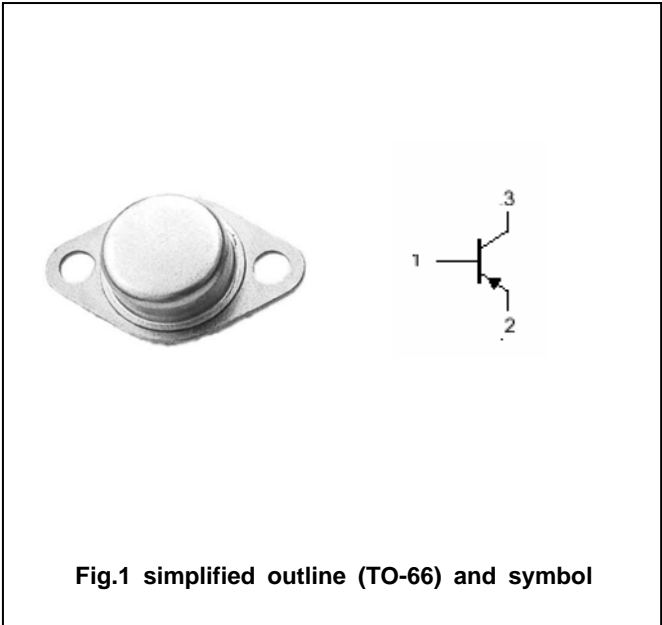
- With TO-66 package
- Complement to type 2SC2239
- High breakdown votage

**APPLICATIONS**

- Power amplifier applications
- Driver stage amplifier applications

**PINNING(See Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



**Absolute maximum ratings(Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-160	V
$V_{CEO}$	Collector-emitter voltage	Open base	-160	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-1.5	A
$I_E$	Emitter current		1.5	A
$P_T$	Total power dissipation	$T_C=25^\circ C$	25	W
$T_j$	Junction temperature		150	°C
$T_{stg}$	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA; I <sub>B</sub> =0	-160			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-1mA; I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-500mA; I <sub>B</sub> =-50mA			-1.5	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-500mA ; V <sub>CE</sub> =-5V			-1.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-160V ; I <sub>E</sub> =0			-1.0	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-1.0	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-100mA ; V <sub>CE</sub> =-5V	70		240	
C <sub>ob</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V, f=1MHz		30		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-100mA ; V <sub>CE</sub> =10V		100		MHz

◆ h<sub>FE</sub> Classifications

O	Y
70-140	120-240

PACKAGE OUTLINE

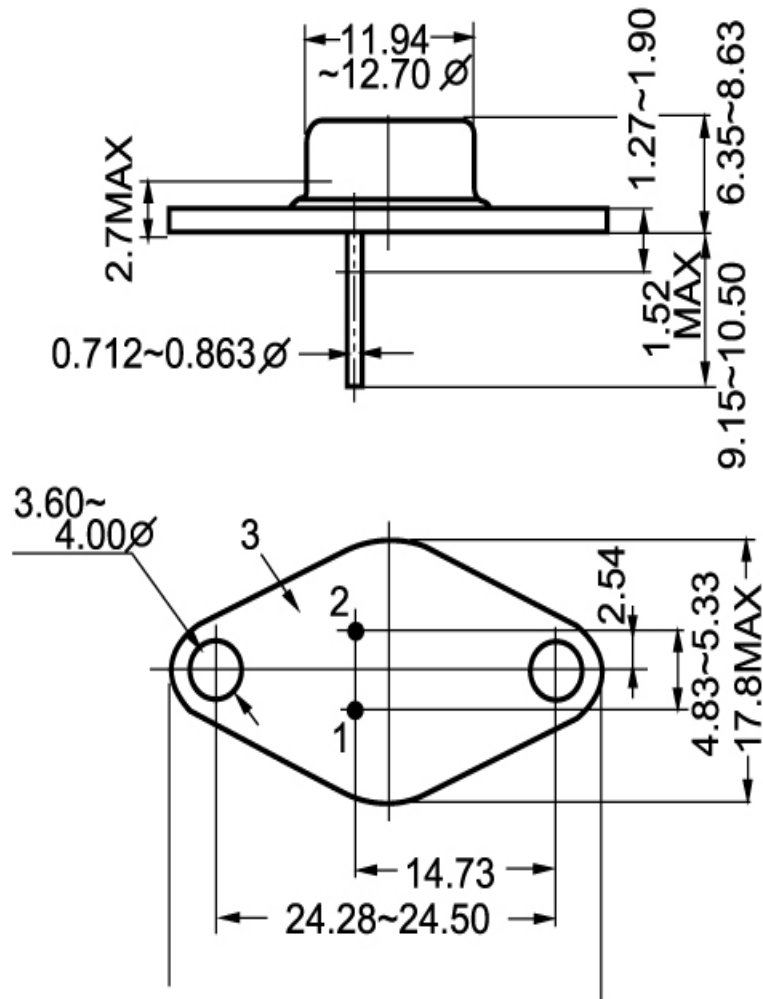


Fig.2 Outline dimensions